

NPN power Darlington transistor

Features

- High current capability
- Fast switching speed
- High DC current gain

Applications

- Linear and switching industrial equipment

Description

The BDW83C is an epitaxial-base NPN power monolithic Darlington transistor mounted in TO-247 plastic package. It is intended for use in power linear and switching applications.

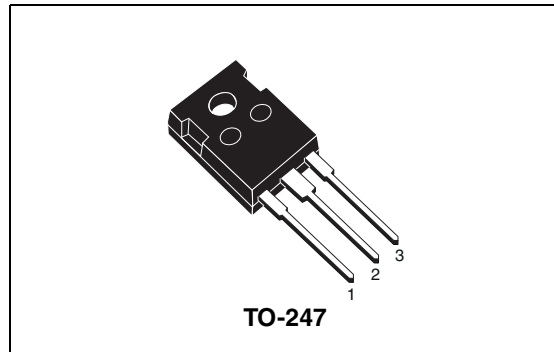


Figure 1. Internal schematic diagram

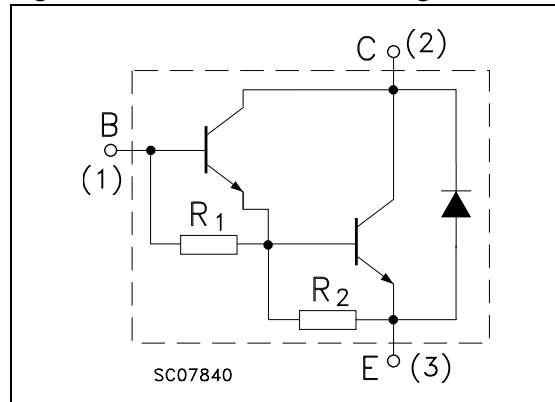


Table 1. Device summary

Order code	Marking	Package	Packaging
BDW83C	BDW83C	TO-247	Tube

1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	100	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	100	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	5	V
I_C	Collector current	15	A
I_{CM}	Collector peak current ($t_p < 5\text{ms}$)	40	A
I_B	Base current	0.5	A
P_{TOT}	Total dissipation at $T_c \leq 25\text{ }^\circ\text{C}$	130	W
T_{stg}	Storage temperature	-65 to 150	$^\circ\text{C}$
T_J	Max. operating junction temperature	150	$^\circ\text{C}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.96	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

($T_{\text{case}} = 25^{\circ}\text{C}$; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_{\text{E}} = 0$)	$V_{\text{CB}} = 100 \text{ V}$ $V_{\text{CB}} = 100 \text{ V}$ $T_{\text{C}} = 150^{\circ}\text{C}$			500 5	μA mA
I_{CEO}	Collector cut-off current ($I_{\text{B}} = 0$)	$V_{\text{CE}} = 40 \text{ V}$			1	mA
I_{EBO}	Emitter cut-off current ($I_{\text{C}} = 0$)	$V_{\text{EB}} = 5 \text{ V}$			2	mA
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = 30 \text{ mA}$	100			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 6 \text{ A}$ $I_{\text{B}} = 12 \text{ mA}$ $I_{\text{C}} = 15 \text{ A}$ $I_{\text{B}} = 150 \text{ mA}$			2.5 4	V V
$V_{\text{BE(on)}}^{(1)}$	Base-emitter on voltage	$I_{\text{C}} = 6 \text{ A}$ $V_{\text{CE}} = 3 \text{ V}$			2.5	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 6 \text{ A}$ $V_{\text{CE}} = 3 \text{ V}$ $I_{\text{C}} = 15 \text{ A}$ $V_{\text{CE}} = 3 \text{ V}$	750 100		20000	
V_{F}	Diode forward voltage	$I_{\text{F}} = 10 \text{ A}$			4	V
t_{on} t_{off}	Resistive load Turn-on time Turn-off time	$V_{\text{CC}} = 30 \text{ V}$ $I_{\text{C}} = 10 \text{ A}$ $I_{\text{B1}} = -I_{\text{B2}} = 40 \text{ mA}$		0.9 6		μs μs

1. Pulsed duration = 300 μs , duty cycle $\leq 1.5\%$.

3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark.

TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	

